WHAT IS CLAIMED IS:

1. A blankmask for extreme ultraviolet (EUV) lithography, comprising a substrate, a reflective film formed on the substrate, a capping film formed on the reflective film, an etch stop film formed on the capping film, and a phase shift film formed on the etch stop film,

the phase shift film containing ruthenium (Ru),

the etch stop film containing chrome (Cr) and niobium (Nb), and

a hard mask film formed on the phase shift film,

wherein the hard mask film contains tantalum (Ta) and oxygen (O), and

content of tantalum (Ta) in the hard mask film is higher than or equal to 50 at%.

2. The blankmask of claim 1, wherein, in the etch stop film, content of niobium (Nb) ranges from 20 to 50 at%, and content of chrome (Cr) ranges from 10 to 40 at%.

3. The blankmask of claim 2, wherein the etch stop film further contains nitrogen (N).

4. The blankmask of claim 3, wherein content of nitrogen (N) in the etch stop film ranges from 10 to 70 at%.

5. The blankmask of claim 4, wherein the etch stop film has a thickness of 15 nm or less.

6. The blankmask of claim 1, wherein the hard mask film further contains boron (B).

7. The blankmask of claim 6, wherein content of boron (B) in the hard mask film is lower than or equal to 20 at%.

8. The blankmask of claim 7, wherein the hard mask film has a thickness of 2 to 5 nm.

9. The blankmask of claim 7, wherein the hard mask film has a reflectivity of 40% or lower with respect to deep ultraviolet (DUV) inspection light having a wavelength of 193 nm.

10. A photomask for extreme ultraviolet (EUV) lithography, prepared using the blankmask of claim 1.

11. A method of preparing a photomask for extreme ultraviolet (EUV) lithography, using the blankmask of claim 1, the method comprising:

a) forming a resist film pattern on the hard mask film;

b) etching the hard mask film by fluorine-based etching gas while using the resist film pattern as an etch mask;

c) removing the resist film pattern;

d) etching the phase shift film by chlorine-based etching gas containing oxygen while using a pattern of the hard mask film as an etch mask; and

e) etching the etch stop film by chlorine-based etching gas containing no oxygen while using the pattern of the hard mask film and a pattern of the phase shift film as etch masks.